

46. The method of claim 45, further comprising:
rewriting data to said plurality of memory cells in response to determining from said first and second read results that the data storage of the memory device is deteriorated.

47. The method of claim 46, wherein the data values written into said plurality of memory cells in said rewriting are determined based on error correction code (ECC).

48. The method of claim 45, wherein said method is part of a programming process.

49. The method of claim 45, wherein said method is part of a reading process.

50. The method of claim 45, wherein said memory cells are multi-state memory cells.

51. The method of claim 45, wherein said memory cells are floating gate transistors and said terminal is a control gate.--